

Fig. 1 (prior art)

200

206

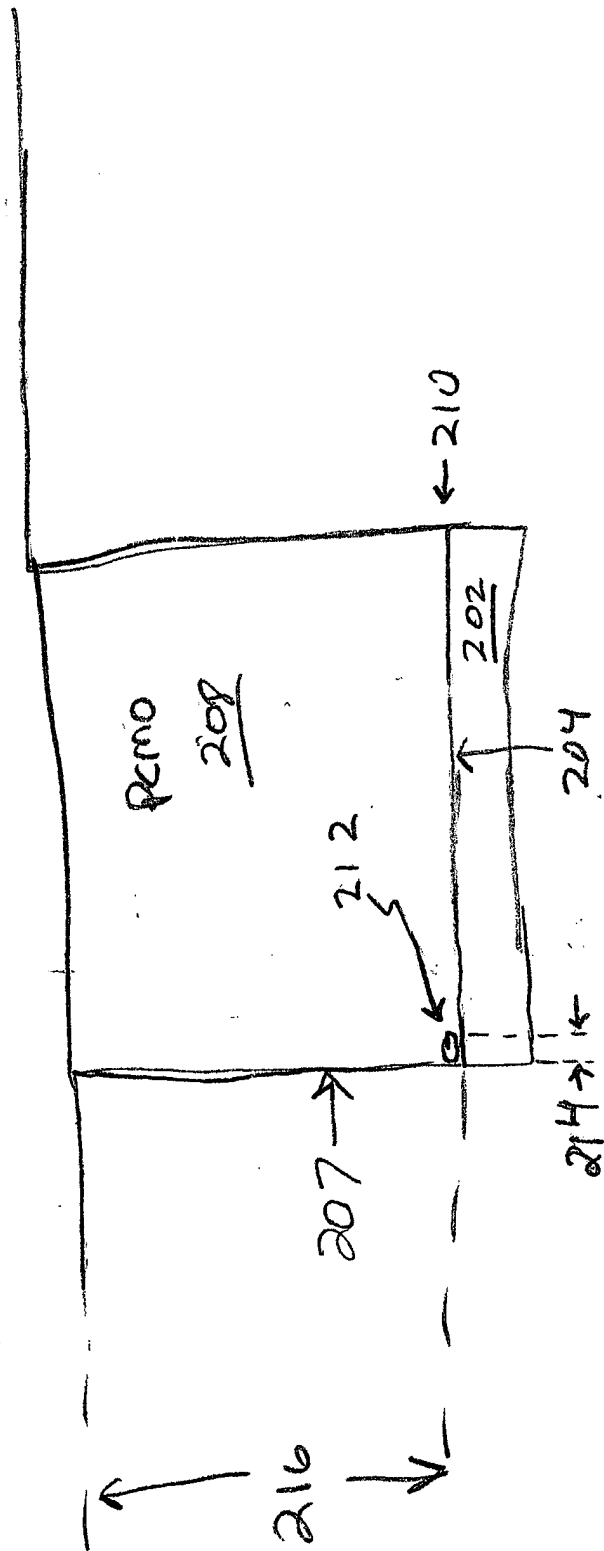
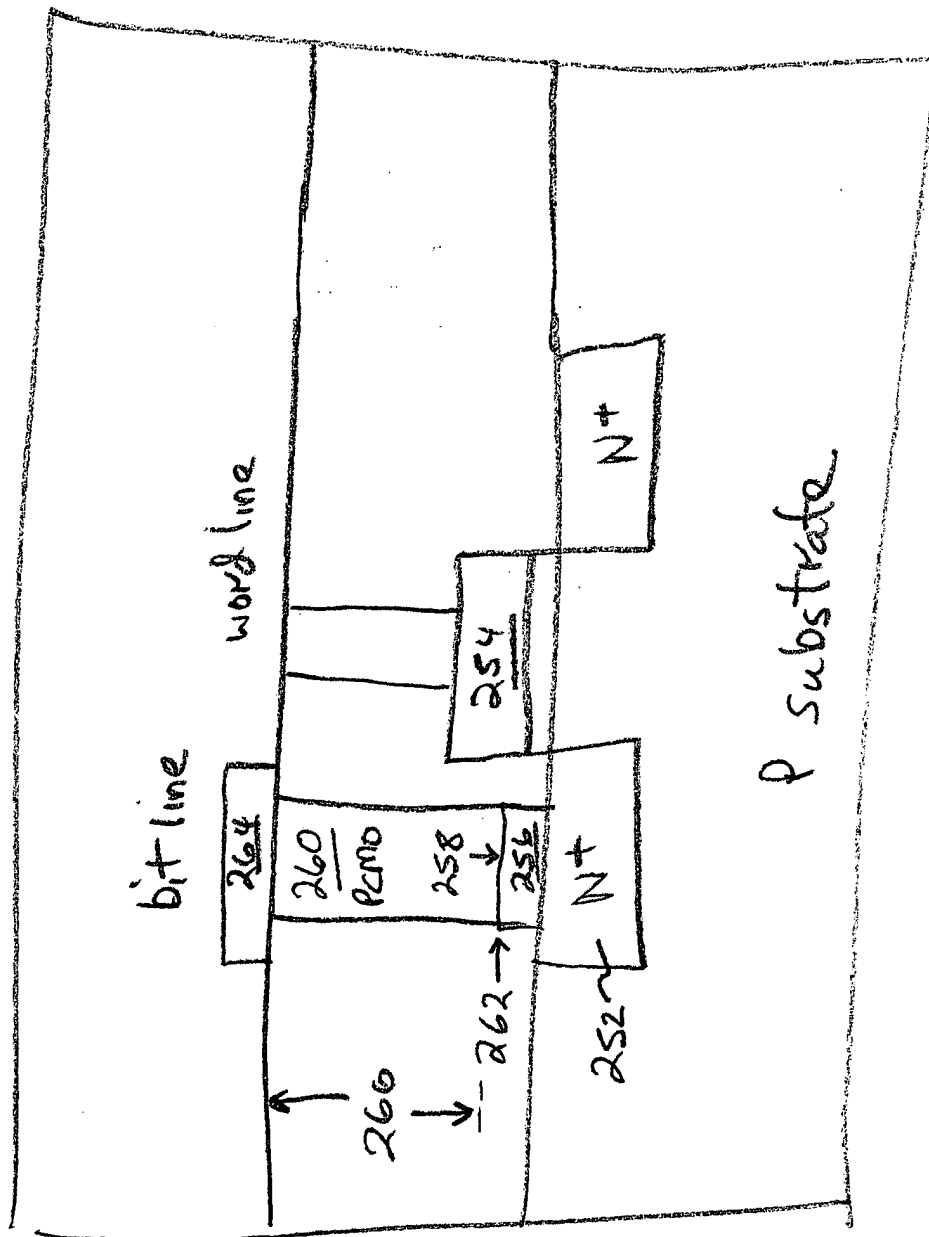


Fig. 2a

Fig. 2b

250  
↓



IRIT memory array

25



acetic acid injected onto water surface

↓  
spin at 1500 to 3000 rpm for 30 seconds

↓  
0.05M PCMO solution injected onto water surface

↓  
Spin at 1500 to 3000 rpm for 30 seconds

↓  
0.25M PCMO solution ←

↓  
injected onto water surface  
(manual or auto dispense)  
spin speed : 1500 rpm

Spin. at 1500 to 3000 rpm  
for 30 seconds

bake at 180°C for 1 minute

bake at 230°C for 1 minute

RTA anneal at 500°C for 5 minutes

↓  
Post anneal at 500-600°C for 1-6 hours  
in dry clean air

2-6  
cycles

Fig. 3

acetic acid injected onto wafer surface

spin at 1500 to 3000 rpm  
for 30 seconds

0.05M PCMO solution injected  
onto wafer surface

spin at 1500 to 3000 rpm  
for 30 seconds

0.25M PCMO solution

Injected onto wafer surface  
(manual or auto dispense)  
spin speed: 500 rpm

spin at 1500 to 3000 rpm  
for 30 seconds

baking at 180 °C for 1 minute

baking at 230 °C for 1 minute

RTA-anneal at 500 °C for 5 minute

post-anneal at 500 - 600 °C for 1 - 6 hours  
in dry clean air

2-6  
cycles

Fig. 4

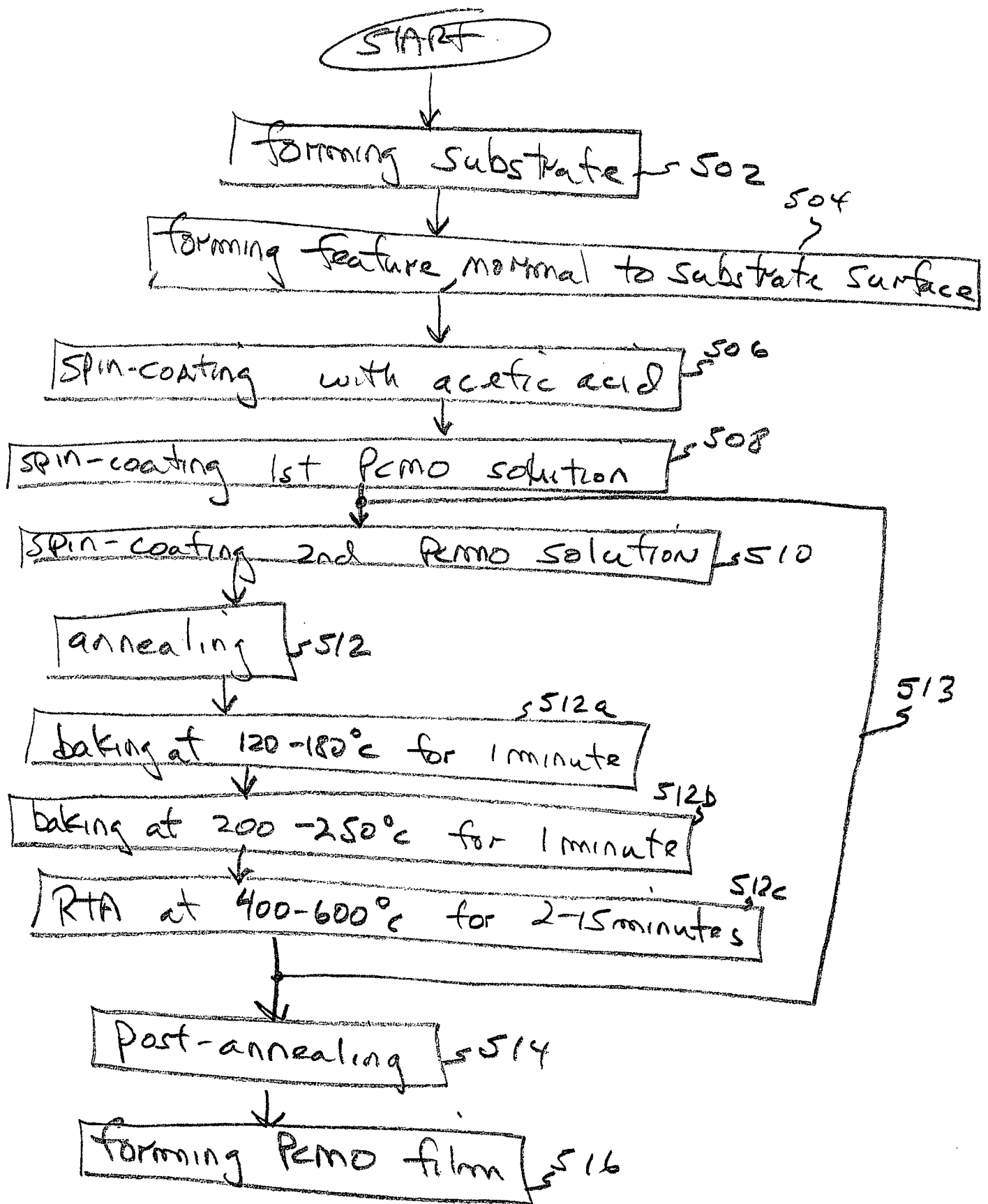


Fig. 5